Analog Power AM20N10-250D MOSFET Datasheet

http://www.manuallib.com/analog-power/am20n10-250d-mosfet-datasheet.html

Key Features:

Low rDS(on) trench technology

Low thermal impedance

Fast switching speed

Typical Applications:

PoE Power Sourcing Equipment

PoE Powered Devices

Telecom DC/DC converters

White LED boost converters

ManualLib.com collects and classifies the global product instrunction manuals to help users access anytime and anywhere, helping users make better use of products.

http://www.manuallib.com

N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

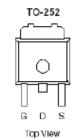
Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- · White LED boost converters

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
100	280 @ V _{GS} = 10V	11		
	355 @ V _{GS} = 4.5V	10		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current	T _C =25°C	I _D	11	Α	
Pulsed Drain Current ^b		I _{DM}	50	^	
Continuous Source Current (Diode Conduction)		I _S	28	Α	
Power Dissipation	T _C =25°C	P_{D}	50	W	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board, drain pad using 2 oz copper, value dependent on PC board thermal characteristics
- b. Pulse width limited by maximum junction temperature

Typical Electrical Characteristics

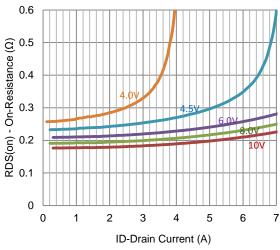
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, ID = 250 uA 1		3.5	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	l	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$			280	mΩ	
Dialii-Source Ori-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 4 \text{ A}$			355	11112	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 4.5 \text{ A}$		5		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 14 \text{ A}, V_{GS} = 0 \text{ V}$		0.95		V	
		Dynamic					
Total Gate Charge	Q_g			3.8			
Gate-Source Charge	Q_gs	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 4.5 \text{ A}$		1.3		nC	
Gate-Drain Charge	Q_{gd}			1.7			
Turn-On Delay Time	t _{d(on)}			4.8			
Rise Time	t _r	V_{DD} = 50 V, R_L = 14.3 Ω , I_D = 4.5 A,		3.9		nS	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		12.7		113	
Fall Time	t _f			3.2			
Input Capacitance	C _{iss}			332			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		40		pF	
Reverse Transfer Capacitance	C_{rss}			29			
Gate Resistance	R_g	f = 1 MHz		0.3		Ω	

Notes

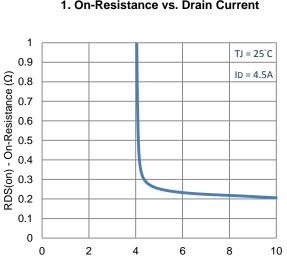
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

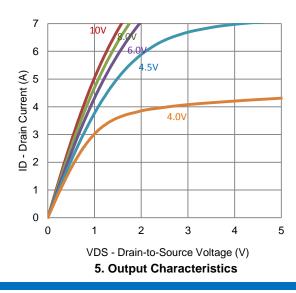
Typical Electrical Characteristics

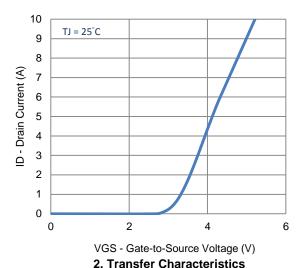


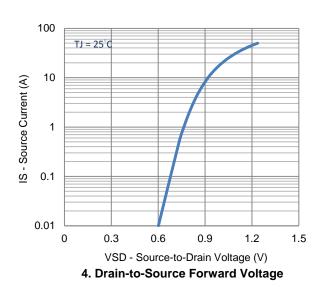
1. On-Resistance vs. Drain Current

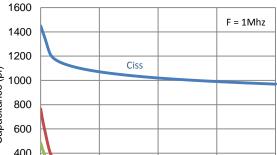


VGS - Gate-to-Source Voltage (V) 3. On-Resistance vs. Gate-to-Source Voltage









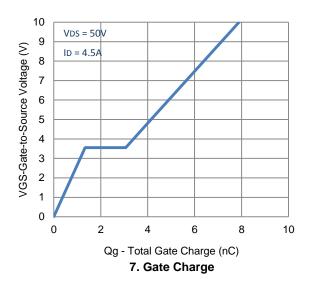
Capacitance (pf) 400 200 Crss 0 0 10 15 20 VDS-Drain-to-Source Voltage (V)

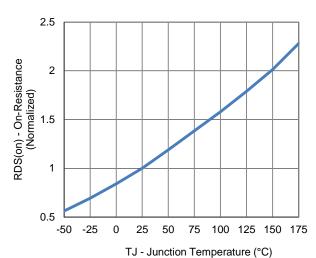
6. Capacitance

© Preliminary

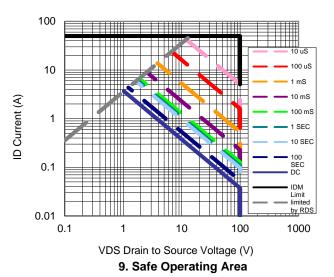
Publication Order Number: DS_AM20N10-250D_1B

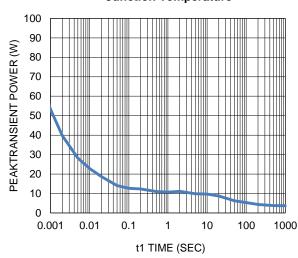
Typical Electrical Characteristics



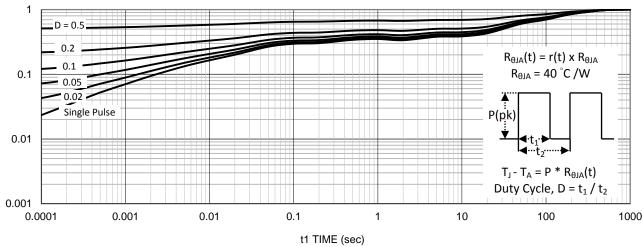


8. Normalized On-Resistance Vs
Junction Temperature



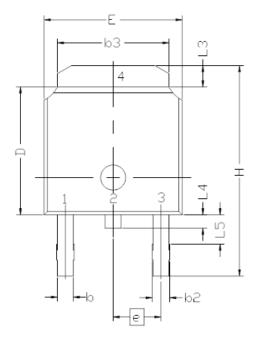


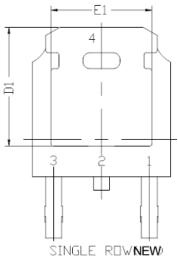
10. Single Pulse Maximum Power Dissipation

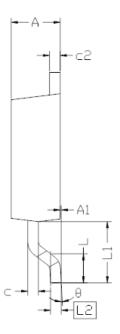


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVMDEL	DIMENS:				
SYMBOL	MIN	NDM	MAX		
E	6.40	6.60	6.731		
L	1.40	1.52	1.77		
L1	2.743 REF				
L2	0.	.508 BS	C C		
L3	0,89		1.27		
L4	0.64		1.01		
L5					
D	6.00	6.10	6,223		
Н	9.40	10.00	10.40		
b	0.64	0.76	0.88		
b2	0.77	0.84	1.14		
b3	5,21	5.34	5.46		
е	2.	286 BS			
Α	2,20	2.30	2,38		
A1	0		0.127		
C	0.45	0.50	0.60		
c2	0.45	0.50	0.58		
D1	5,30				
E1	4.40				
А	U.		10*		

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.